- 3-Terminal Regulators
- Output Current up to 100 mA
- No External Components
- Internal Thermal-Overload Protection
- Internal Short-Circuit Current Limiting
- Direct Replacements for Fairchild μA78L00 Series

description

This series of fixed-voltage integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. In addition, they can be used with power-pass elements to make high-current voltage regulators. One of these regulators can deliver up to 100 mA of output current. The internal limiting and thermal-shutdown features of these regulators make them essentially immune to overload. When used as a replacement for a zener diode-resistor combination, an effective improvement in output impedance can be obtained, together with lower bias current.

The μ A78L00C series is characterized for operation over the virtual junction temperature range of 0°C to 125°C.

OUTPUT 1 8 INPUT COMMON 2 7 COMMON NC 4 5 NC

LP PACKAGE

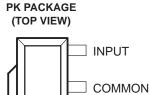
NC - No internal connection

(TOP VIEW) | INPUT | COMMON

OUTPUT

OUTPUT

TO-226AA





				PACKAGE	D DEVICES			
TJ	VO(NOM)	SMALL O			SOT- (Pk		CHIP FORM	
•	(*)			OUTPUT VOLTA	GE TOLERANC			(Y)
		5%	10%	5%	10%	5%	10%	
	2.6	μΑ78L02ACD	_	μΑ78L02ACLP	μΑ78L02CLP	μΑ78L02ACPK	μΑ78L02CPK	μΑ78L02Y
1	5	μA78L05ACD	μΑ78L05CD	μA78L05ACLP	μA78L05CLP	μΑ78L05ACPK	μΑ78L05CPK	μΑ78L05Υ
1	6.2	μΑ78L06ACD	μΑ78L06CD	μΑ78L06ACLP	μΑ78L06CLP	μΑ78L06ACPK	μΑ78L06CPK	μΑ78L06Y
0°C to	8	μA78L08ACD	μA78L08CD	μA78L08ACLP	μΑ78L08CLP	μΑ78L08ACPK	μΑ78L08CPK	μΑ78L08Υ
125°C	9	μΑ78L09ACD	μΑ78L09CD	μΑ78L09ACLP	μΑ78L09CLP	μΑ78L09ACPK	μΑ78L09CPK	μΑ78L09Y
	10	μΑ78L10ACD	_	μA78L10ACLP	μΑ78L10CLP	μΑ78L10ACPK	μΑ78L10CPK	μΑ78L10Y
	12	μA78L12ACD	μΑ78L12CD	μA78L12ACLP	μA78L12CLP	μΑ78L12ACPK	μΑ78L12CPK	μΑ78L12Y
	15	μΑ78L15ACD	μΑ78L15CD	μΑ78L15ACLP	μΑ78L15CLP	μΑ78L15ACPK	μΑ78L15CPK	μΑ78L15Y

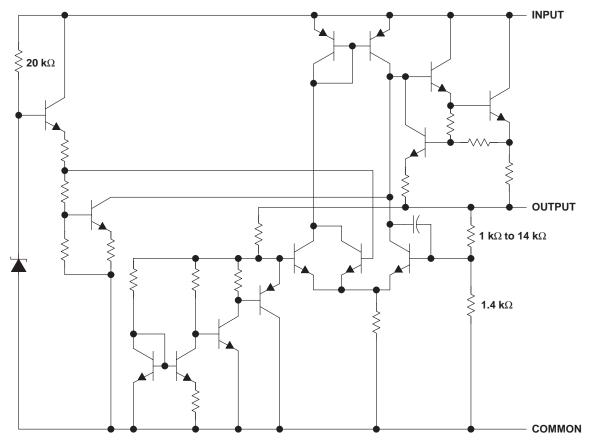
D and LP packages are available taped and reeled. Add the suffix R to the device type (e.g., μ A78L05ACDR). The PK package is only available taped and reeled (e.g., μ A78L02ACPKR). Chip forms are tested at T_A = 25°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



schematic



NOTE: Resistor values shown are nominal.

absolute maximum ratings over operating temperature range (unless otherwise noted)†

		μ Α78Lxx	UNIT
Input voltage V.	μΑ78L02AC, μΑ78L05C-μΑ78L09C, μΑ78L10AC	30	V
Input voltage, V _I	μΑ78L12C, μΑ78L12AC, μΑ78L15C, μΑ78L15AC	35	V
	D package	97	
Package thermal impedance, θ _{JA} (see Notes 1 and 2)	LP package	156	°C
	PK package	52	
Virtual junction temperature range, TJ		0 to 150	°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 second	onds	260	°C
Storage temperature range, T _{Stg}		-65 to 150	°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can impact reliability. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal-overload protection may be activated at power levels slightly above or below the rated dissipation.
 - 2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions

		MIN	MAX	UNIT
	μΑ78L02AC	4.75	20	
	μΑ78L05C, μΑ78L05AC	7	20	
	μΑ78L06C, μΑ78L06AC	8.5	20	
lanut valtara V	μΑ78L08C, μΑ78L08AC	10.5	23	V
Input voltage, V _I	μΑ78L09C, μΑ78L09AC	11.5	24	V
	μΑ78L10AC	12.5	25	
	μΑ78L12C, μΑ78L12AC	14.5	27	
	μΑ78L15C, μΑ78L15AC	17.5	30	
Output current, IO	•		100	mA
Operating virtual junction temperature, TJ		0	125	°C

electrical characteristics at specified virtual junction temperature, V_I = 9 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST C	ONDITIONS	- +	μ Α	478L02C	;	UNIT
PARAMETER	IESI C	ONDITIONS	ΤJ [†]	MIN	TYP	MAX	UNIT
	V 4.75 V to 20 V	l - 1 - 1 - 10 - 10 - 10	25°C	2.5	2.6	2.7	
Output voltage	$V_I = 4.75 \text{ V to } 20 \text{ V},$	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	2.45		2.75	V
	$I_O = 1 \text{ mA to } 70 \text{ mA}$		0°C to 125°C	2.45		2.75	
lanut valtage regulation	V _I = 4.75 V to 20 V		25°C		20	100	mV
Input voltage regulation	V _I = 5 V to 20 V		25-0		16	75	IIIV
Ripple rejection	V _I = 6 V to 20 V,	f = 120 Hz	25°C	43	51		dB
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$		25°C		12	50	mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		25 C		6	25	IIIV
Output noise voltage	f = 10 Hz to 100 kHz		25°C		30		μV
Dropout voltage			25°C		1.7		V
Bias current			25°C		3.6	6	mA
Dias current			125°C			5.5	IIIA
Bias current change	V _I = 5 V to 20 V		0°C to 125°C			2.5	mA
bias current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$		0 0 10 125 0			0.1	IIIA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 10 V, I_O = 40 mA (unless otherwise noted)

DADAMETED	TEST CONDITIONS	T.1	μ	A78L050	;	μ Α	78L05A	С	UNIT
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	77/10 00 7/ 10 10 10 10 10 10	25°C	4.6	5	5.4	4.8	5	5.2	
Output voltage	$V_I = 7 \text{ V to } 20 \text{ V}, \qquad I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	4.5		5.5	4.75		5.25	V
	I _O = 1 mA to 70 mA	0°C to 125°C	4.5		5.5	4.75		5.25	
Input	V _I = 7 V to 20 V	25°C		32	200		32	150	mV
voltage regulation	V _I = 8 V to 20 V	25°C		26	150		26	100	mv
Ripple rejection	V _I = 8 V to 18 V, f = 120 Hz	25°C	40	49		41	49		dB
Output	I _O = 1 mA to 100 mA	25°C		15	60		15	60	mV
voltage regulation	I _O = 1 mA to 40 mA	25°C		8	30		8	30	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		42			42		μV
Dropout voltage		25°C		1.7			1.7		V
Dies sument		25°C		3.8	6		3.8	6	A
Bias current		125°C		•	5.5			5.5	mA
Bias	V _I = 8 V to 20 V	000 40 40500			1.5			1.5	A
current change	I _O = 1 mA to 40 mA	0°C to 125°C			0.2			0.1	mA

[†] Pulse-testing techniques maintain TJ as close to TA as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



electrical characteristics at specified virtual junction temperature, V_I = 12 V, I_O = 40 mA (unless otherwise noted)

DADAMETER	TEST CONDITIONS	T.1	μ.	478L060	;	μ Α	78L06A	С	UNIT
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	UNII
	V 05 V 12 00 V 1 4 22 A 12 A 22 A	25°C	5.7	6.2	6.7	5.95	6.2	6.45	
Output voltage	$V_{\rm I} = 8.5 \text{ V to } 20 \text{ V}, I_{\rm O} = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	5.6		6.8	5.9		6.5	V
	I _O = 1 mA to 70 mA	0°C to 125°C	5.6		6.8	5.9		6.5	
Input	V _I = 8.5 V to 20 V	25°C		35	200		35	175	mV
voltage regulation	V _I = 9 V to 20 V	25 C		29	150		29	125	IIIV
Ripple rejection	V _I = 10 V to 20 V, f = 120 Hz	25°C	39	48		40	48		dB
Output	I _O = 1 mA to 100 mA	25°C		16	80		16	80	mV
voltage regulation	I _O = 1 mA to 40 mA	25 C		9	40		9	40	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		46			46		μV
Dropout voltage		25°C		1.7			1.7		V
Bias current		25°C		3.9	6		3.9	6	mA
bias current		125°C			5.5			5.5	mA
Bias	V _I = 9 V to 20 V	0°C to 105°C			1.5			1.5	A
current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C			0.2			0.1	mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	ΤJ [†]	μ	478L080	;	μΑ	78L08A	С	UNIT
PARAMETER	TEST CONDITIONS	1,1,1	MIN	TYP	MAX	MIN	TYP	MAX	UNII
	V 40.5 V/42.02 V 1 4 mA 42.40 mA	25°C	7.36	8	8.64	7.7	8	8.3	
Output voltage	$V_I = 10.5 \text{ V to } 23 \text{ V}, I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	7.2		8.8	7.6		8.4	V
	I _O = 1 mA to 70 mA	0°C to 125°C	7.2		8.8	7.6		8.4	
Input voltage	V _I = 10.5 V to 23 V	25°C		42	200		42	175	mV
regulation	V _I = 11 V to 23 V	25 C		36	150		36	125	IIIV
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz	25°C	36	46		37	46		dB
Output voltage	I _O = 1 mA to 100 mA	25°C		18	80		18	80	mV
regulation	I _O = 1 mA to 40 mA	25 C		10	40		10	40	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		54			54		μV
Dropout voltage		25°C		1.7			1.7		V
Bias current		25°C		4	6		4	6	mA
bias current		125°C			5.5			5.5	IIIA
Bias	V _I = 5 V to 20 V	0°C to 125°C			1.5			1.5	mA
current change	I _O = 1 mA to 40 mA	0°C to 125°C			0.2			0.1	IIIA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



electrical characteristics at specified virtual junction temperature, V_I = 16 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	t	μ	478L090	;	μ Α	78L09A	С	UNIT
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	V. 40 V to 24 V . I - 4 m to 40 m t	25°C	8.3	9	9.7	8.6	9	9.4	
Output voltage	$V_{I} = 12 \text{ V to } 24 \text{ V}, I_{O} = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	8.1		9.9	8.55		9.45	V
	I _O = 1 mA to 70 mA	0°C to 125°C	8.1		9.9	8.55		9.45	
Input	V _I = 12 V to 24 V	25°C		45	225		45	175	mV
voltage regulation	V _I = 13 V to 24 V	25°C		40	175		40	125	IIIV
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz	25°C	36	45		38	45		dB
Output	I _O = 1 mA to 100 mA	25°C		19	90		19	90	mV
voltage regulation	I _O = 1 mA to 40 mA	25°C		11	40		11	40	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		58			58		μV
Dropout voltage		25°C		1.7			1.7		V
Dies surrent		25°C		4.1	6		4.1	6	A
Bias current		125°C			5.5			5.5	mA
Bias	V _I = 13 V to 24 V	0°C to 125°C			1.5			1.5	mA
current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0 0 10 125 0			0.2			0.1	IIIA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_{I} = 14 V, I_{O} = 40 mA (unless otherwise noted)

PARAMETER	TEST C	ONDITIONS	- +	μΑ	78L10A	С	UNIT
PARAMETER	IESI C	ONDITIONS	T _J †	MIN	TYP	MAX	UNIT
	V. 42 V to 25 V	l - 1 m Λ to 10 m Λ	25°C	9.6	10	10.4	
Output voltage	$V_{I} = 13 \text{ V to } 25 \text{ V},$	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	9.5		10.5	V
	$I_O = 1 \text{ mA to } 70 \text{ mA}$		0°C to 125°C	9.5		10.5	
Input voltage regulation	V _I = 13 V to 25 V		25°C		51	175	mV
Input voltage regulation	V _I = 14 V to 25 V		25°C		42	125	IIIV
Ripple rejection	$V_{I} = 15 \text{ V to } 25 \text{ V},$	f = 120 Hz	25°C	37	44		dB
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$		25°C		20	90	mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		25 0		11	40	IIIV
Output noise voltage	f = 10 Hz to 100 kHz		25°C		62		μV
Dropout voltage			25°C		1.7		V
Bias current			25°C		4.2	6	mA
Dias curient			125°C			5.5	IIIA
Bias current change	V _I = 14 V to 25 V		0°C to 125°C			1.5	mA
bias current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	·	0 0 10 125 0			0.1	IIIA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



electrical characteristics at specified virtual junction temperature, V_I = 19 V, I_O = 40 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	T.:t	μ	A78L120	;	μΑ	78L12A	С	UNIT
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
	V. 44.V.ta 27.V. I.a. 4 m A to 40 m A	25°C	11.1	12	12.9	11.5	12	12.5	
Output voltage	$V_I = 14 \text{ V to } 27 \text{ V}, I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	10.8		13.2	11.4		12.6	V
	I _O = 1 mA to 70 mA	0°C to 125°C	10.8		13.2	11.4		12.6	
Input	V _I = 14.5 V to 27 V	25°C		55	250		55	250	mV
voltage regulation	V _I = 16 V to 27 V	25°C		49	200		49	200	IIIV
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz	25°C	36	42		37	42		dB
Output	I _O = 1 mA to 100 mA	25°C		22	100		22	100	mV
voltage regulation	I _O = 1 mA to 40 mA	25 C		13	50		13	50	IIIV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		70			70		μV
Dropout voltage		25°C		1.7			1.7		V
Bias current		25°C		4.3	6.5		4.3	6.5	mA
bias current		125°C			6			6	IIIA
Bias	V _I = 16 V to 27 V	0°C to 125°C			1.5			1.5	mA
current change	$I_O = 1 \text{ mA to } 40 \text{ mA}$	0 0 10 125 0			0.2			0.1	IIIA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 40 mA (unless otherwise noted)

DADAMETED	TEST CONDITIONS	T.#	μ.	A78L150	;	μΑ	78L15A	C	UNIT
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	MIN	TYP	MAX	UNII
_	V 47.5 V to 20 V	25°C	13.8	15	16.2	14.4	15	15.6	
Output voltage	$V_I = 17.5 \text{ V to } 30 \text{ V}, \qquad I_O = 1 \text{ mA to } 40 \text{ mA}$	0°C to 125°C	13.5		16.5	14.25		15.75	V
voltage	I _O = 1 mA to 70 mA	0°C to 125°C	13.5		16.5	14.25		15.75	
Input	V _I = 17.5 V to 30 V			65	300		65	300	>/
voltage regulation	V _I = 20 V to 30 V	25°C		58	250		58	250	mV
Ripple rejection	V _I = 18.5 V to 28.5 V, f = 120 Hz	25°C	33	39		34	39		dB
Output	I _O = 1 mA to 100 mA	0500		25	150		25	150	\/
voltage regulation	I _O = 1 mA to 40 mA	25°C		15	75		15	75	mV
Output noise voltage	f = 10 Hz to 100 kHz	25°C		82			82		μV
Dropout voltage		25°C		1.7			1.7		٧
Bias current		25°C		4.6	6.5		4.6	6.5	mA
DIAS CUITETIL		125°C			6			6	IIIA
Bias	V _I = 10 V to 30 V	0°C to 125°C			1.5			1.5	mA
current change	I _O = 1 mA to 40 mA	0 0 10 125 0			0.2			0.1	111/4

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



electrical characteristics at specified virtual junction temperature, $V_I = 9 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	μ Α	78L02Y	,	UNIT
PARAMETER	TEST CONDITIONS!	MIN	TYP	MAX	UNII
Output voltage			2.6		V
Input voltage regulation	V _I = 4.75 V to 20 V		20		mV
Input voltage regulation	V _I = 5 V to 20 V		16		IIIV
Ripple rejection	$V_{I} = 6 \text{ V to } 20 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$		51		dB
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$		12		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		6		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		30		μV
Dropout voltage			1.7		V
Bias current			3.6		mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 10 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONST	μ Α78L05Y	UNIT		
PARAMETER	TEST CONDITIONS!	MIN TYP MAX	I UNII		
Output voltage		5	V		
lanut valtage regulation	V _I = 7 V to 20 V	32	m)/		
Input voltage regulation	V _I = 8 V to 20 V	26	mV		
Ripple rejection	$V_{I} = 8 \text{ V to } 18 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$	49	dB		
Output voltage regulation	I _O = 1 mA to 100 mA	15	mV		
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	8	1111		
Output noise voltage	f = 10 Hz to 100 kHz	42	μV		
Dropout voltage		1.7	V		
Bias current		3.8	mA		

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 12 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ.	UNIT				
PARAMETER	TEST CONDITIONS!	MIN	TYP	MAX	ONIT		
Output voltage			6.2		V		
Input voltage regulation	V _I = 8.5 V to 20 V		35		m\/		
Input voltage regulation	V _I = 9 V to 20 V		29		mV		
Ripple rejection	$V_{ } = 10 \text{ V to } 20 \text{ V}, \qquad f = 120 \text{ Hz}$		48		dB		
Output voltage regulation	$I_O = 1 \text{ mA to } 100 \text{ mA}$	16		mV			
Output voitage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		9		IIIV		
Output noise voltage	f = 10 Hz to 100 kHz		46		μV		
Dropout voltage			1.7		V		
Bias current			3.9	·	mA		

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



electrical characteristics at specified virtual junction temperature, $V_I = 14 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	μ Α 7	UNIT		
PARAMETER	TEST CONDITIONS!	MIN	TYP	MAX	UNII
Output voltage			8		V
Input voltage regulation	V _I = 10.5 V to 23 V	42	mV		
Input voltage regulation	V _I = 11 V to 23 V	36			
Ripple rejection	$V_{I} = 13 \text{ V to } 23 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$		46		dB
Output voltage regulation	I _O = 1 mA to 100 mA		18		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		10		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		54		μV
Dropout voltage			1.7		V
Bias current			4		mA

T Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 16 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†	μ Α78L09Y	UNIT		
PARAMETER	TEST CONDITIONS!	MIN TYP MAX			
Output voltage		9	V		
lanut voltage regulation	V _I = 12 V to 24 V	45	\/		
Input voltage regulation	V _I = 13 V to 24 V	40	mV		
Ripple rejection	$V_I = 15 \text{ V to } 25 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$	45	dB		
Output voltage regulation	I _O = 1 mA to 100 mA	19	mV		
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	11	IIIV		
Output noise voltage	f = 10 Hz to 100 kHz	58	μV		
Dropout voltage		1.7	V		
Bias current		4.1	mA		

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33- μ F capacitor across the input and a 0.1- μ F capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 40 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	μ Α78L10Y	UNIT
PARAMETER	TEST CONDITIONS!	MIN TYP MAX	ן וואט
Output voltage		10	V
Input voltage regulation	V _I = 13 V to 25 V	51	mV
	V _I = 14 V to 25 V	42] ""
Ripple rejection	$V_{I} = 15 \text{ V to } 25 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$	44	dB
Output voltage regulation	I _O = 1 mA to 100 mA	20	mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	11] ""
Output noise voltage	f = 10 Hz to 100 kHz	62	μV
Dropout voltage		1.7	V
Bias current		4.2	mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



electrical characteristics at specified virtual junction temperature, $V_I = 19 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	μ Α78L12Y			UNIT
PARAMETER	TEST CONDITIONS!	MIN	TYP	MAX	UNIT
Output voltage			12		V
Input voltage regulation	V _I = 14.5 V to 27 V		55	55	mV
Input voltage regulation	V _I = 16 V to 27 V		49		IIIV
Ripple rejection	$V_{I} = 15 \text{ V to } 25 \text{ V}, \qquad \qquad f = 120 \text{ Hz}$		42		dB
Output voltage regulation	I _O = 1 mA to 100 mA		22		mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$		13		IIIV
Output noise voltage	f = 10 Hz to 100 kHz		70		μV
Dropout voltage			1.7	, and the second	V
Bias current			4.3	·	mA

The Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33- μ F capacitor across the input and a 0.1- μ F capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 23 \text{ V}$, $I_O = 40 \text{ mA}$, $T_J = 25^{\circ}\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	μ Α78L15Y	UNIT
PARAMETER	TEST CONDITIONS!	MIN TYP MAX	וואט [
Output voltage		15	V
Input voltage regulation	V _I = 17.5 V to 30 V	65	mV
	$V_I = 20 \text{ V to } 30 \text{ V}$	58] ''''
Ripple rejection	V _I = 18.5 V to 28.5 V, f = 120 Hz	39	dB
Output voltage regulation	I _O = 1 mA to 100 mA	25	mV
Output voltage regulation	$I_O = 1 \text{ mA to } 40 \text{ mA}$	15] ""
Output noise voltage	f = 10 Hz to 100 kHz	82	μV
Dropout voltage		1.7	V
Bias current		4.6	mA

[†] Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



APPLICATION INFORMATION

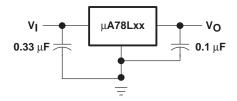


Figure 1. Fixed-Output Regulator

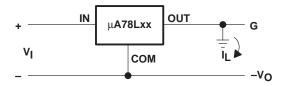


Figure 2. Positive Regulator in Negative Configuration (V_I Must Float)

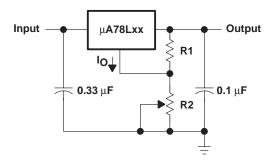


Figure 3. Adjustable-Output Regulator

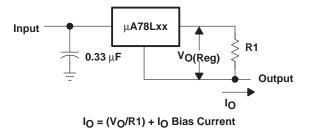


Figure 4. Current Regulator

APPLICATION INFORMATION

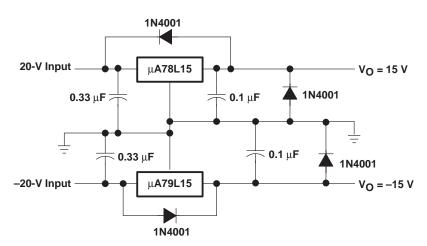


Figure 5. Regulated Dual Supply

operation with a load common to a voltage of opposite polarity

In many cases, a regulator powers a load that is not connected to ground but, instead, is connected to a voltage source of opposite polarity (e.g., operational amplifiers, level-shifting circuits, etc.). In these cases, a clamp diode should be connected to the regulator output as shown in Figure 6. This protects the regulator from output polarity reversals during startup and short-circuit operation.

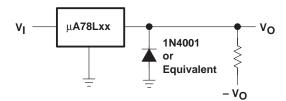


Figure 6. Output Polarity-Reversal-Protection Circuit

reverse-bias protection

Occasionally, the input voltage to the regulator can collapse faster than the output voltage. This can occur, for example, when the input supply is crowbarred during an output overvoltage condition. If the output voltage is greater than approximately 7 V, the emitter-base junction of the series-pass element (internal or external) could break down and be damaged. To prevent this, a diode shunt can be employed as shown in Figure 7.

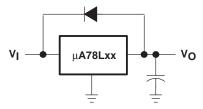


Figure 7. Reverse-Bias-Protection Circuit



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